



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
100V	$6.0\Omega @ V_{GS} = 10V$	0.17A

Description and Applications

These N-Channel enhancement mode field effect transistors are produced using DIODES proprietary, high density, uses advanced trench technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as:

- Small Servo Motor Control
- Power MOSFET Gate Drivers
- Switching Applications

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating

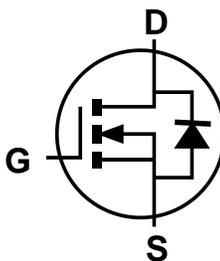
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

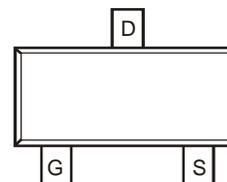
SOT23



Top View



Equivalent Circuit



Top View

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	I _D	170	mA
	I _{DM}	680	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P _D	300	mW
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	0.1	μA	V _{DS} = 100V, V _{GS} = 0V
		-	-	30	μA	V _{DS} = 100V, V _{GS} = 0V @ T _A = +150°C (Note 7)
		-	-	10	nA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage, Forward	I _{GSSF}	-	-	50	nA	V _{GS} = 20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.8	1.4	2.0	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	6.0	Ω	V _{GS} = 10V, I _D = 0.17A
		-	-	10		V _{GS} = 4.5V, I _D = 0.17A
Forward Transfer Admittance	g _{FS}	80	370	-	ms	V _{DS} = 10V, I _D = 0.17A, f = 1.0KHz
Diode Forward Voltage	V _{SD}	-	0.84	1.3	V	V _{GS} = 0V, I _S = 0.34A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{ISS}	-	22	60	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	-	3.5	15		
Reverse Transfer Capacitance	C _{RSS}	-	2.0	6		
SWITCHING CHARACTERISTICS (Note 7)						
Turn-On Delay Time	t _{D(ON)}	-	-	8	ns	V _{GS} = 10V, V _{DD} = 30V, I _D = 0.28A, R _{GEN} = 50Ω
Turn-On Rise Time	t _R	-	-	8		
Turn-Off Delay Time	t _{D(OFF)}	-	-	13		
Turn-Off Fall Time	t _F	-	-	16		

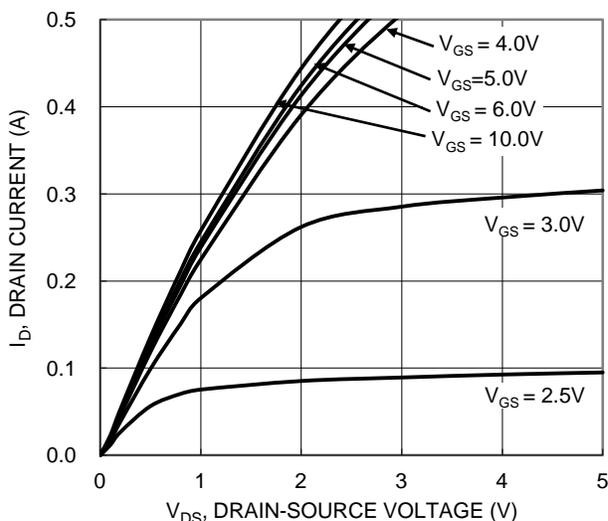


Figure 1. Typical Output Characteristic

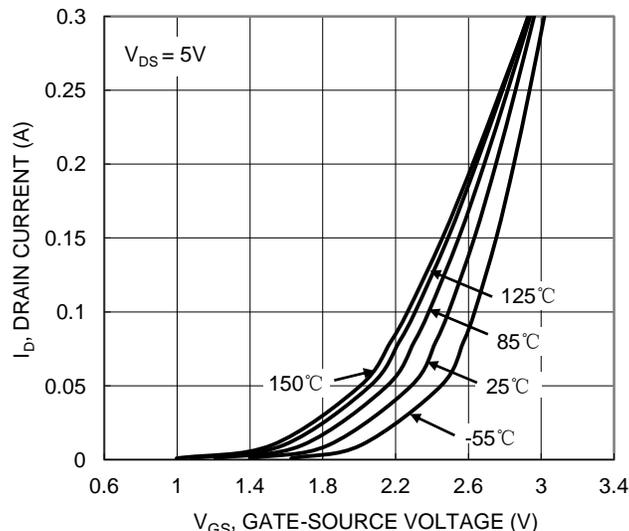


Figure 2. Typical Transfer Characteristic

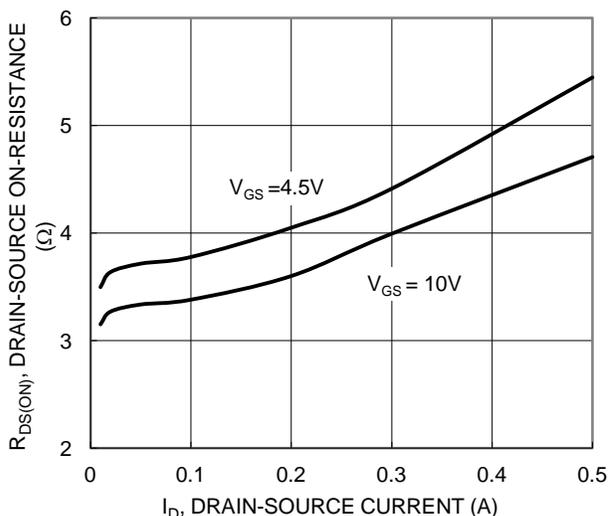


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

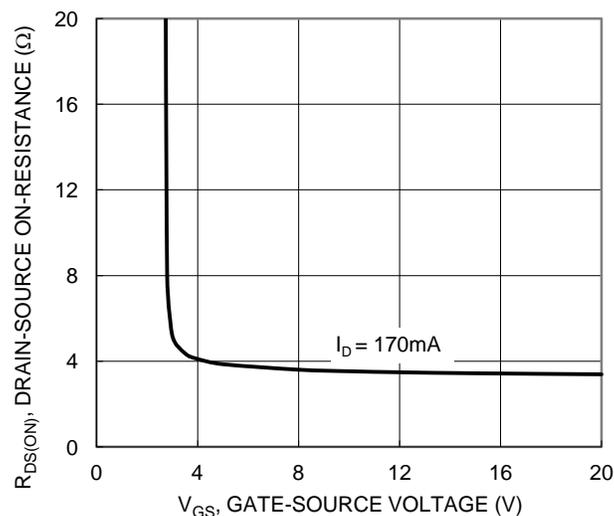


Figure 4. Typical Transfer Characteristic

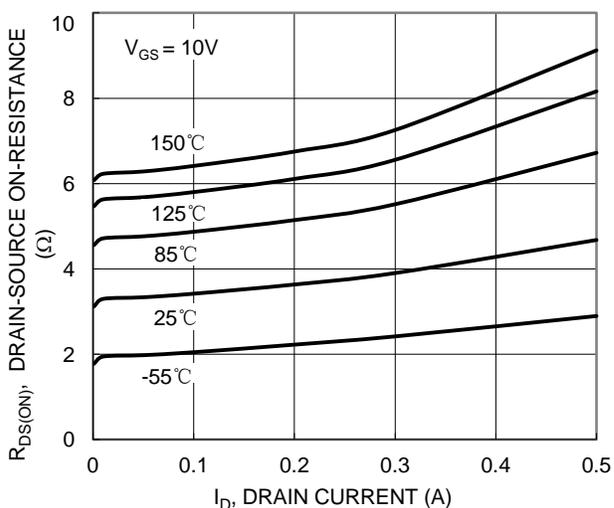


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

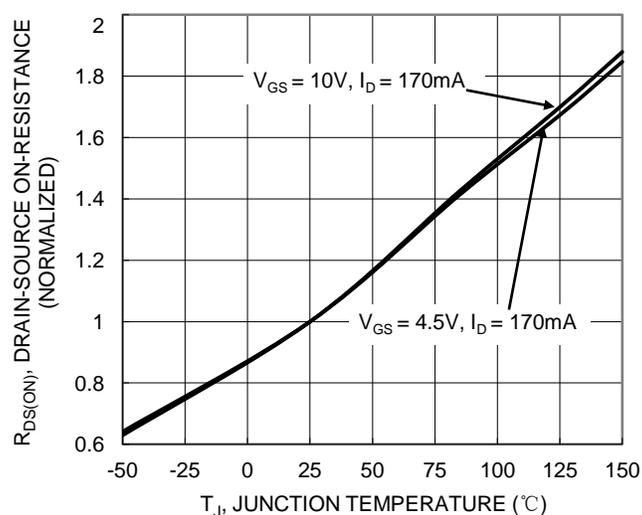


Figure 6. On-Resistance Variation with Junction Temperature

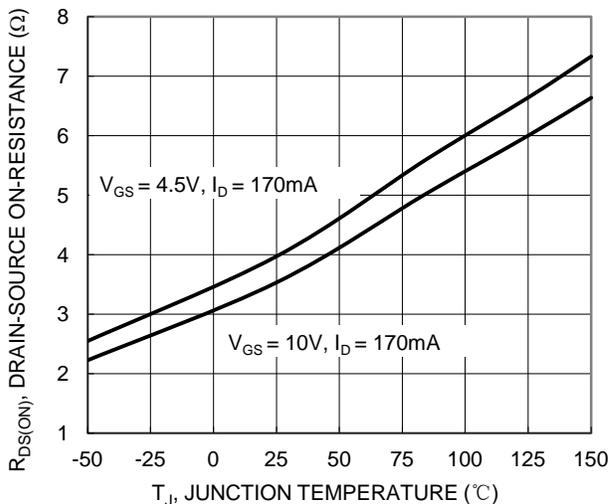


Figure 7. On-Resistance Variation with Junction Temperature

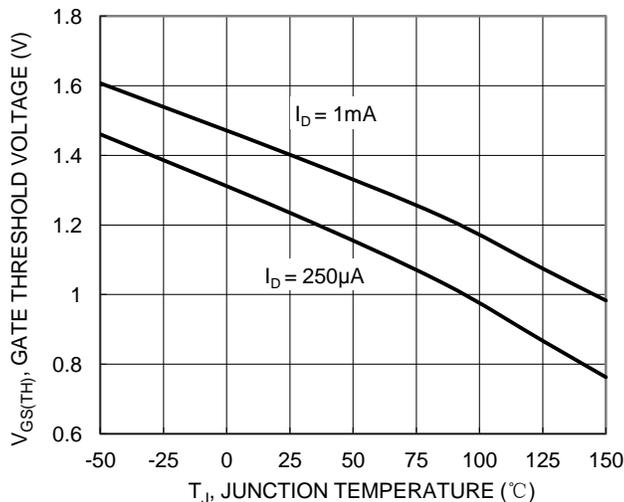


Figure 8. Gate Threshold Variation vs. Junction Temperature

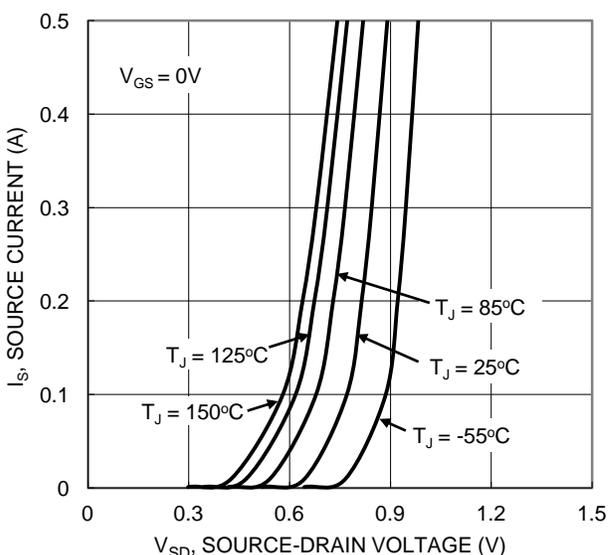


Figure 9. Diode Forward Voltage vs. Current

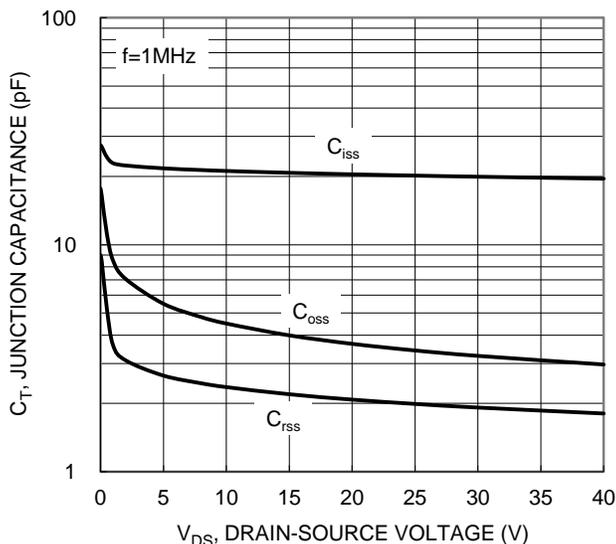


Figure 10. Typical Junction Capacitance

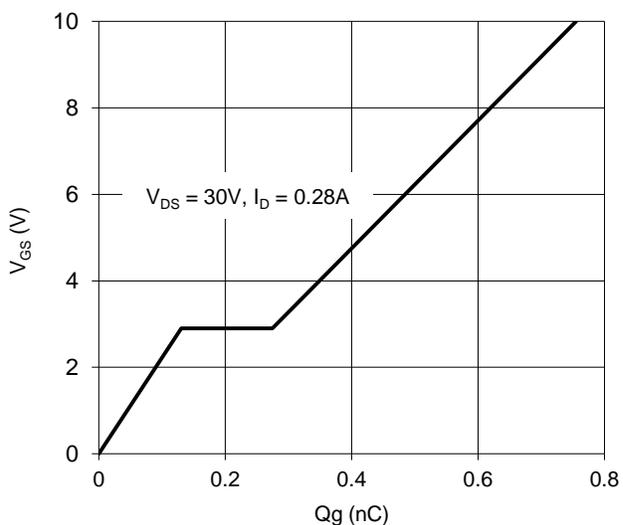


Figure 11. Gate Charge

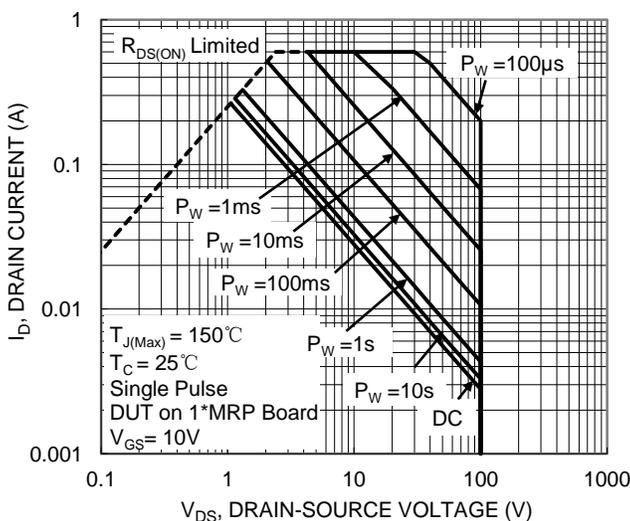


Figure 12. SOA, Safe Operation Area

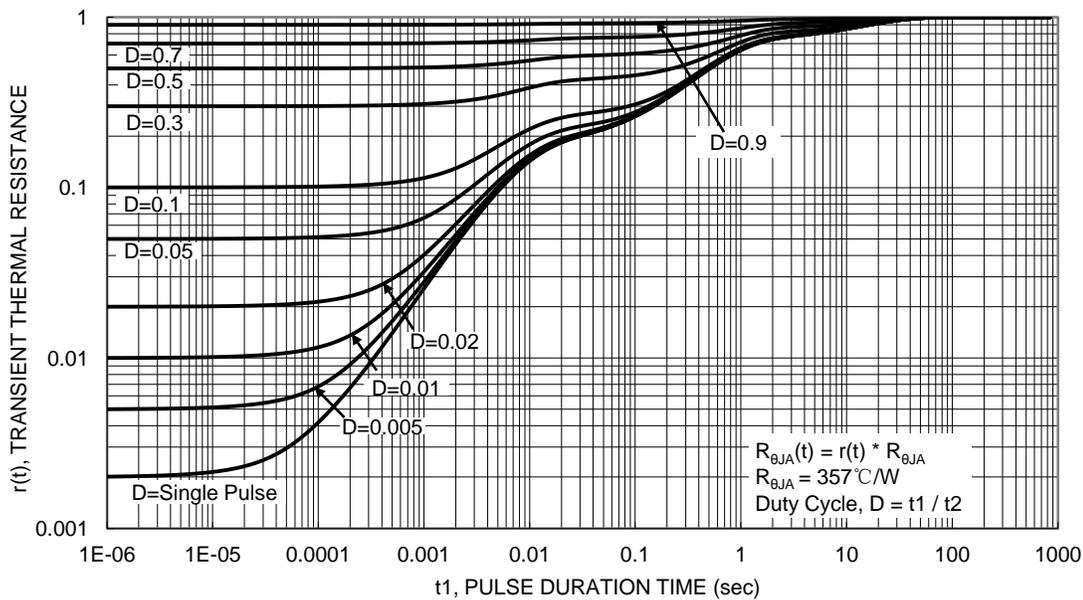
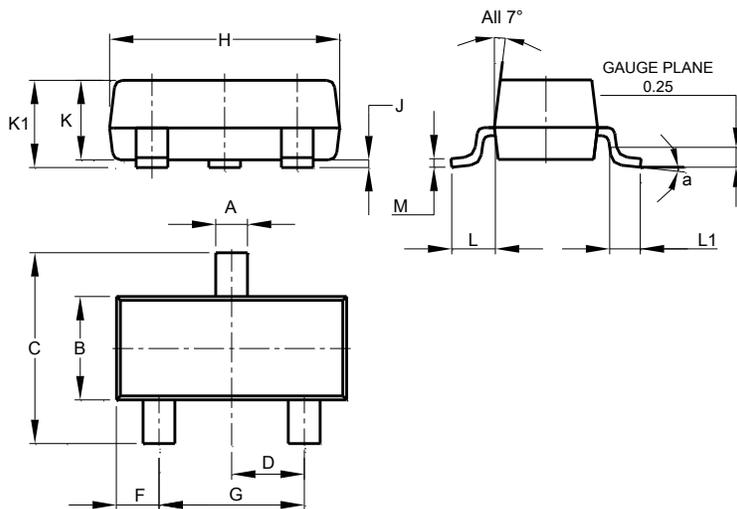


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

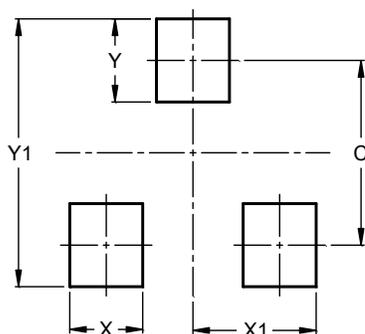
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9